

FORM PTO 1449 (modified)

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U.S. DEPARTMENT OF COMMERCE
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(Use several sheets if necessary)

APPLICANT WU et al.

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GROUP ~~2844~~ 2891

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
JUN. 09 2004						

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

AKS	Y. Honda et al.; "Selective Area Growth Of GaN Microstructure On Patterned (111) and (001) Si Substrates"; <i>Journal of Crystal Growth</i> 230; pp. 346-350; 2001
	B. Beaumont et al; "Lateral Overgrowth Of GaN On Patterned GaN/Sapphire Substrate Via Selective Metal Organic Vapour Phase Epitaxy: A Route to Produce Self Supported GaN Substrates"; <i>Journal of Crystal Growth</i> 189/190 pp. 97-102; 1998
	Jaime A. Freitas, et al.; "Optical And Structural Properties Of Lateral Epitaxial Overgrown GaN Layers"; <i>Journal of Crystal Growth</i> 189/190; pp. 92-96; 1998
	Shuji Nakamura et al.; "Present Status Of InGaN/GaN/AlGaIn-based Laser Diodes"; <i>Journal of Crystal Growth</i> 189/190; pp. 820-825; 1998
	Kazumasa Hiramatsu et al; "Selective Area Growth And Epitaxial Lateral Overgrowth of GaN by Metalorganic Vapor Phase Epitaxy and Hydride Vapor Phase Epitaxy"; <i>Materials Science and Engineering B59</i> ; pp. 104-111; 1999
	Tsvetanka S. Zheleva, et al.; "Lateral Epitaxy and Dislocation Density Reduction in Selectively Grown GaN Structures"; <i>Journal of Crystal Growth</i> 222; pp. 706-718; 2001
	W. S. Wong et al.; "In XGa _{1-x} N Light Emitting Diodes on Si Substrates Fabricated by Pd-In Metal Bonding and Laser Lift-off"; <i>Applied Physics Letters</i> Volume 77; Number 18; pp. 2822-2824; 2000
AKS	Mitsuru Funato et al.; "Integration of GaN With Si Using a AuGe-Mediated Wafer Bonding Technique"; <i>Applied Physics Letters</i> Volume 77; Number 24; pp. 3959-3961; 2000

EXAMINER

Ashe Umman Sarhan

DATE CONSIDERED

6/8/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.